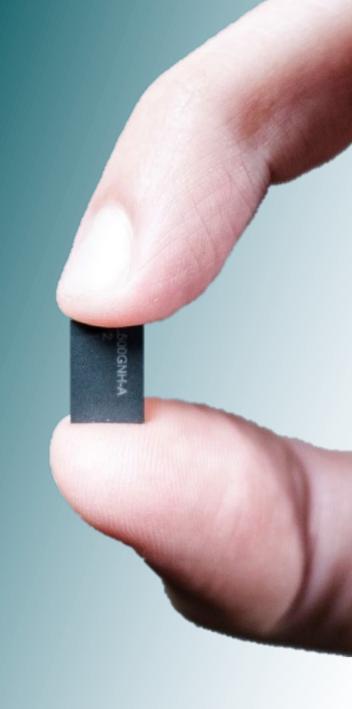
PwrSoC 21 Invited Talk



Power Interposer Technology (PIT)

A Platform for PSiP and PwrSoC Applications Yasser Nour and Hoa Thanh Le

Contact: Yasser Nour, PhD CEO and Co-Founder ynour@lotus-microsystems.com

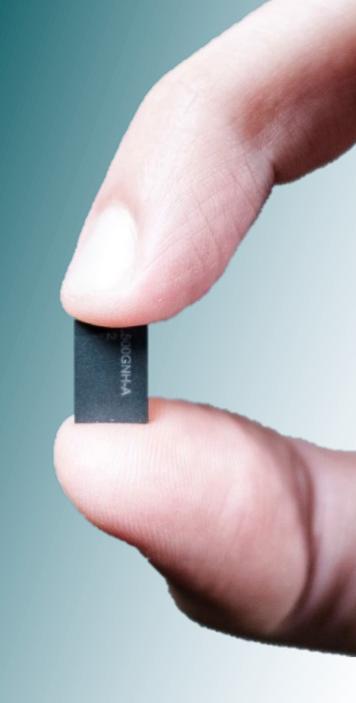


PwrSoC 21 Invited Talk



Power Interposer Technology (PIT)

Part1: Introduction



About Lotus Microsystems



- Founded in 2020 as a spin-out from the Technical University of Denmark (DTU).
- Core IP includes several inventions and a wide range of best practices.
- Cost-effective fab-less manufacturing setup with validated industrial suppliers.
- A team with extensive domain expertise from research, product development, manufacturing and business development.

MISSION

We introduce innovative technology & energy-efficient power supply units. to accelerate technological advances in electronic devices.

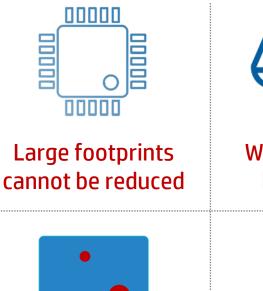
VISION

We develop power converters with higher efficiency, lower space, lower weight, and eco-friendly alternatives to existing materials that work in conjunction with the UN sustainability goals.

Why do we need integrated power converters?

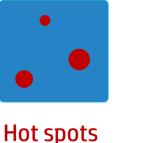


Existing low-current power conversion technologies are <u>reaching the physical boundaries</u> for further Miniaturization!





Weight cannot be reduced



Low efficiency = short battery life



temperatures persist

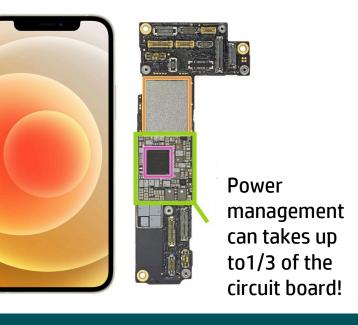


EXAMPLE 1: HEARING AID



Must fit into the ear canal – every mm³ counts!

EXAMPLE 2 : MOBILE PHONE

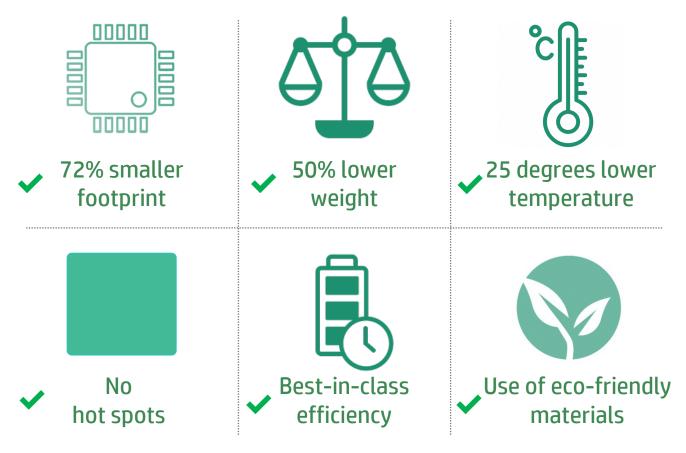


prevail

Solution



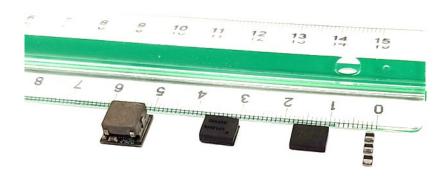
We have replaced the conventional materials with silicon – a cheap, natural resource which is easy to process.



The world's smallest 5V/1A Buck Converter



voltage & current scalable Converters



Power Converters Integration



Integration Level						
Discrete	Module	Power Supply	Power Supply			
Solutions	Integration	in Package	on Chip			
<u>Discrete Controller, Drivers,</u>	<u>Discrete ICs, Ls, Tx, Cs on</u>	<u>Co-packaged ICs, Ls, Cs</u>	Integrated converter			
<u>Switches, Ls, Tx, Cs on PCB</u>	<u>PCB</u>	on substrate or lead-frame	on a single silicon die			
<u>Wired or Header Connectivity</u>	<u>Solderable to the application</u>	<u>Solderable to the application</u>	Stand alone component or			
<u>to the application board</u>	<u>board</u>	<u>board</u>	Integrated with the load			
Die Oiiiiiiiiiiiiiiiiiiiiiiiiiiiiiiiiiiii	Image: Non-StructureImage: Non-StructureDTULotusElektro**Microsystems	(a) UFL ***	Total Total Fudan Uni ****			

* 26V-32V to 50V Class-E Boost Converter

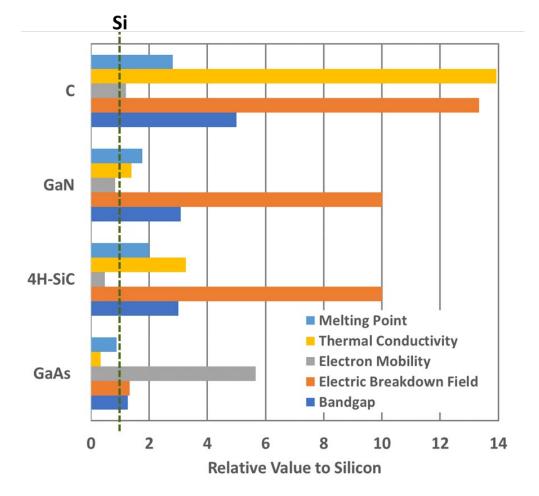
** 80V eGaN Based Buck Power Stage with Integrated Inductor

Inductor *** 3.6V Buck Converter with Power Inductor in-Silicon **** 3.3V Fully integrated buck converter

Technologies [Emerging Technologies]







Technology Independent Switch FOMs

The 3 famous figures of merits

$$FOM_1 = Q_{gtot} \cdot R_{on}$$

$$FOM_2 = Q_{gd} \cdot R_{on}$$

$$FOM_3 = Q_{oss} \cdot R_{on}$$

For power ICs

$$FOM_{RSP} = Area \cdot R_{on}$$

Reflects device size (fabrication cost)

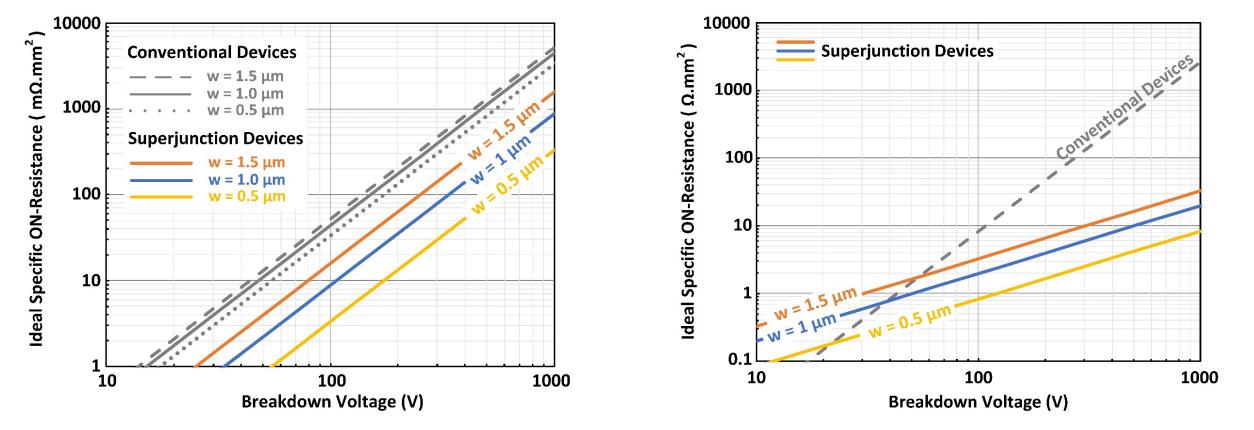
• No single FoM can be used alone to optimize converter performance

Technologies [Silicon Switches]



Majority carrier vertical silicon devices

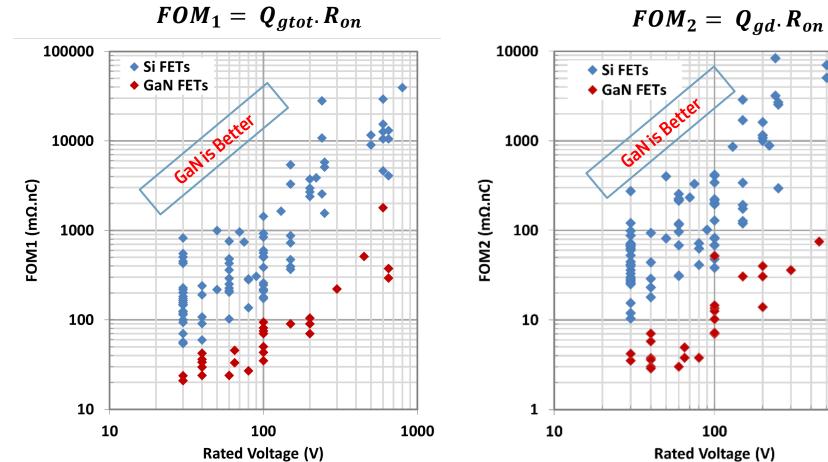
Majority carrier lateral silicon devices



<u>Equations from</u> T. Fujihira, "Theory of Semiconductor Superjunction Devices," Jpn. J. Appl. Phys., no. 36, pp. 6254–6262, 1997

Technologies [GaN FETs Vs. Si FETs]



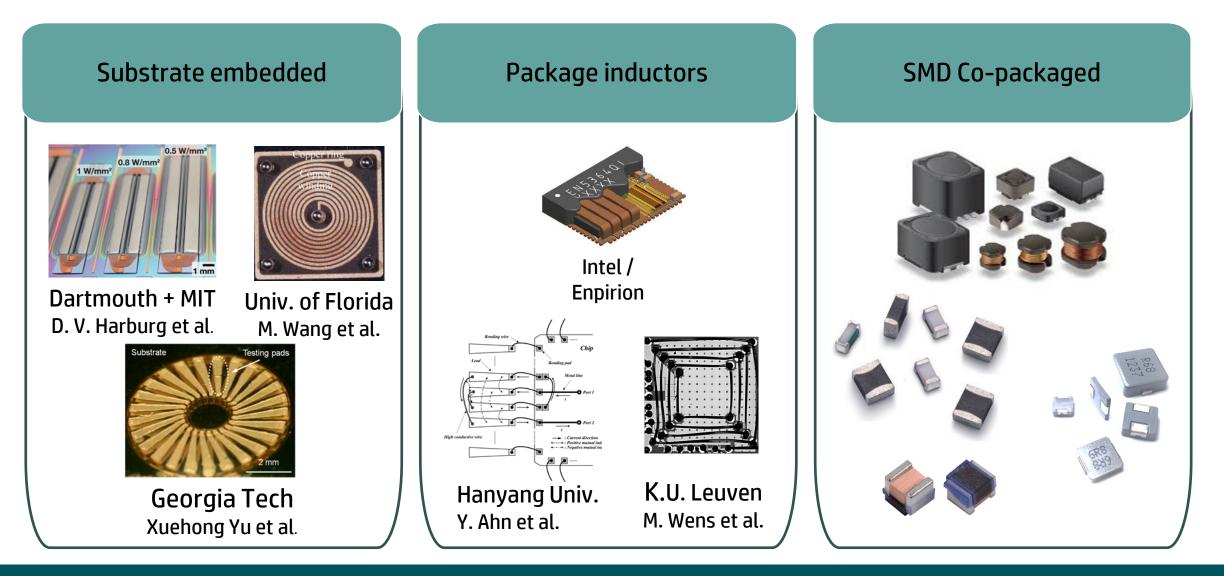


GaN is expected to dominate in terms of performance for 12V+ applications

1000

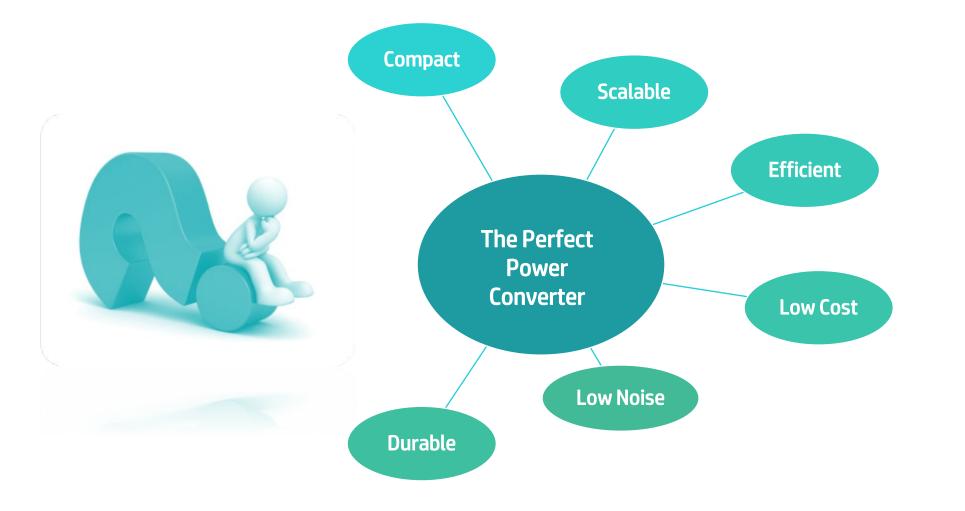
Inductors for PSiP and PwrSoC





Integration goals





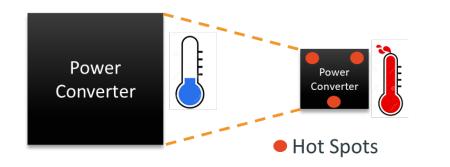
Leveraging the advances in all building components of a power supply

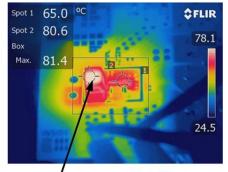
Miniaturization - Thermal Problems



For processing the same output power:

- The smaller the converter size, the higher operating temperatures we observe.
- Smaller integrated components leads to hot spots.





Ceramic-core Hot Spots Inductor

	Substrate Material	λ (W/m-K)	٤ _r	Notes
Ceramic	Alumina (Al ₂ O ₃)	24	9.8-10	Cheaper
	Aluminum Nitride (AIN)	170	9	Expensive
	Beryllia (BeO)	209-330	6.1-7.5	Carcinogenic
	Silicon nitride (Si ₃ Ni ₄)	90	7.5	-
	ZrO ₂ doped Alumina	26	No-data	-
FR4	RO4003C (Rogers Corp.)	0.71	3.38	HF
	FR408 (isola group)	0.4	3.69	High-Tg
	DE104 (isola group)	0.36	4.46	FR4



The Power Interposer technology is a heterogeneous integration platform that features:

- 1- Superior thermal performance
- 2- Usage of best-in-class power converter components
- 4- Three-dimensional integration
- 3- Cost-effective process

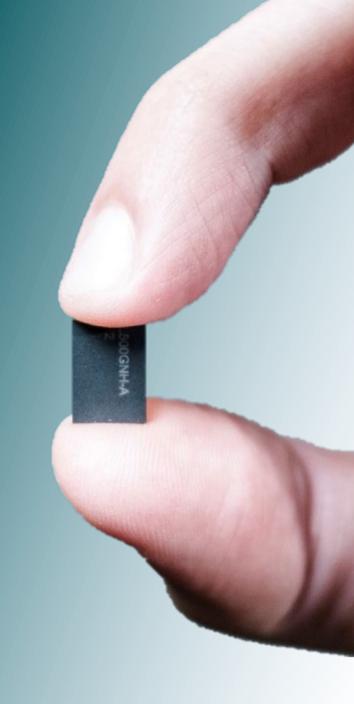
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	DE104 (isola group)	0.36	4.46	FR4
Si	Silicon	100-170	-	-

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Power Interposer Technology (PIT)

Part2: What is PIT ?



About The Technology



Power interposer technology enables a range of distinct benefits.

Why Silicon

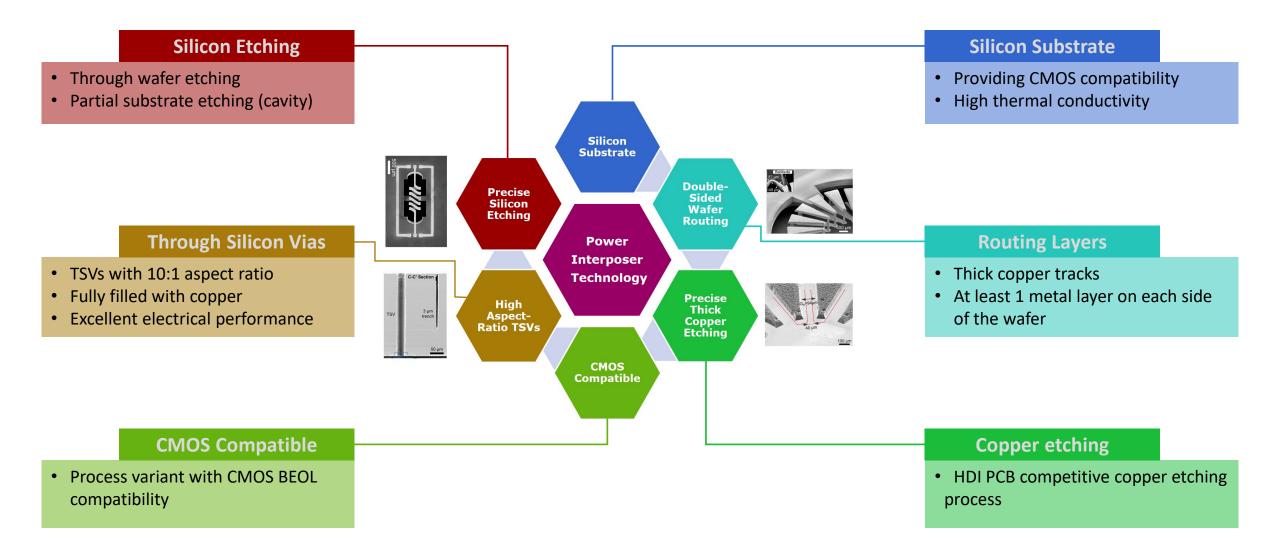
- CMOS Compatible
- High thermal conductivity (hot spot mitigation)
- Silicon is cheap and abundant natural resource (low cost)

Benefits

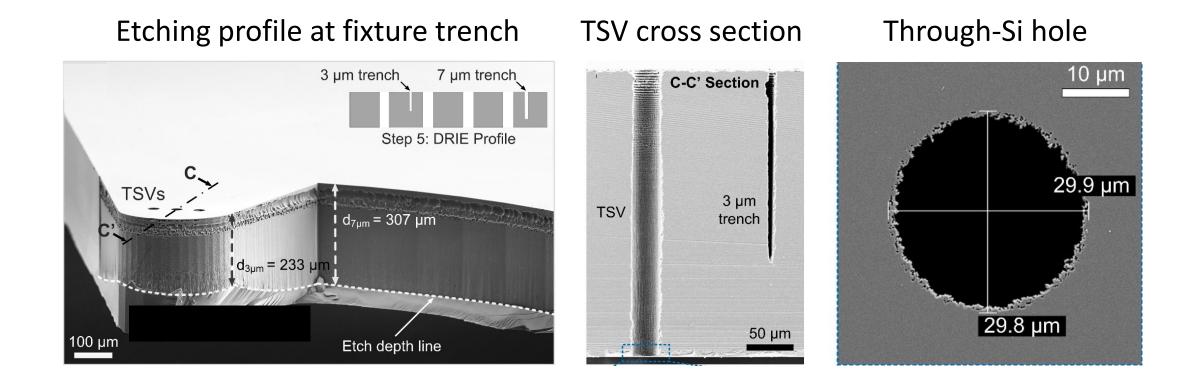
- Smaller power converters ✓
- Superior thermal performance ✓
- Voltage and current scalable \checkmark
- Eco-friendly profile using less copper, no fibreglass ✓

Power Interposer Technology (PIT)



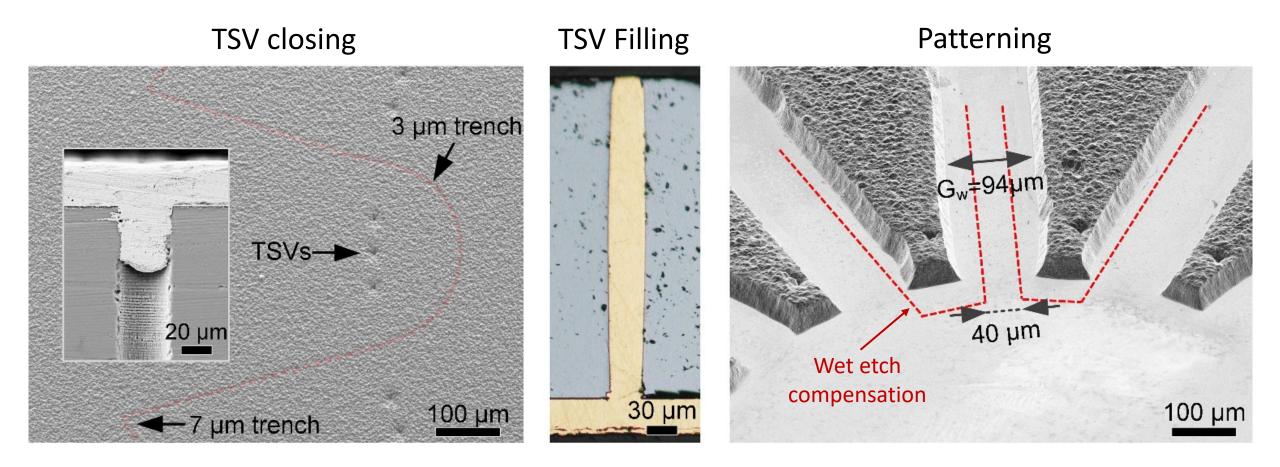






Copper Electroplating and Etching



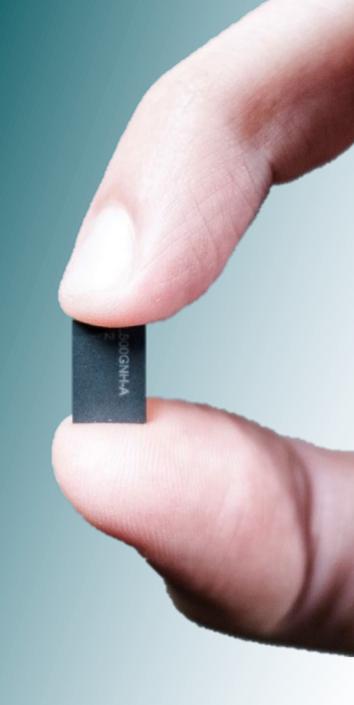


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Power Interposer Technology (PIT)

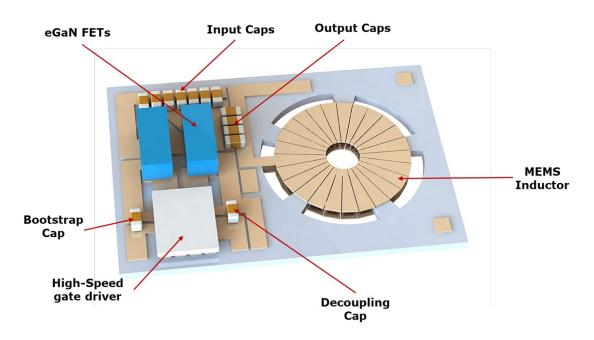
Part3: PIT Applications?

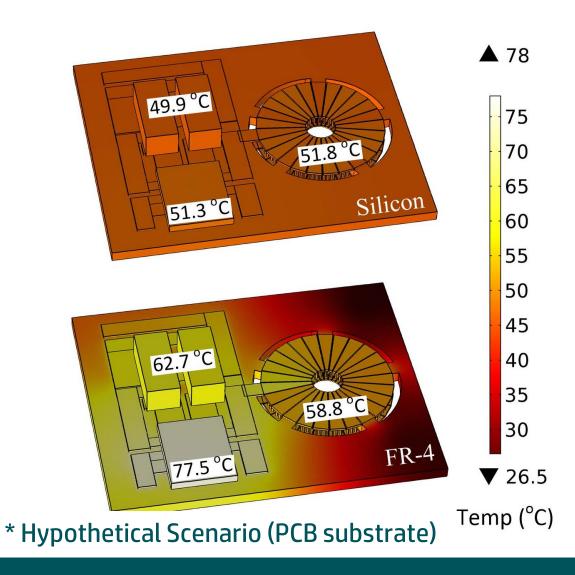


1st Power Interposer – Technical Univ. of Denmark 2018 ULOTUS

Concept Design and Modeling

21 MHz Gan Based Buck converter on Silicon Interposer





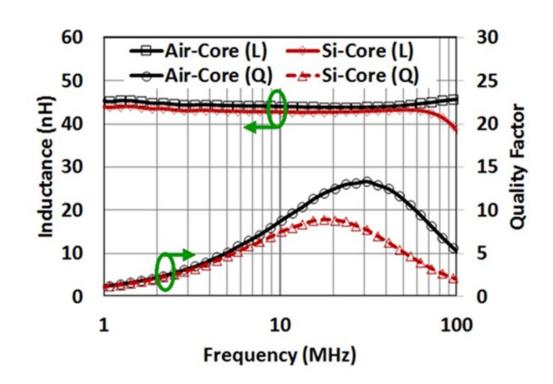
4.5 m

1st Power Interposer – Technical Univ. of Denmark 2018 UCROSYSTEMS

Date 34 Jul 201 Time 11:15(24

Prototype Fabrication Results

Air-core / Si-Core Toroidal Inductors



Inductive Interposer Concept 4.5 x 8 x 0.28 mm

Side

Top

Side

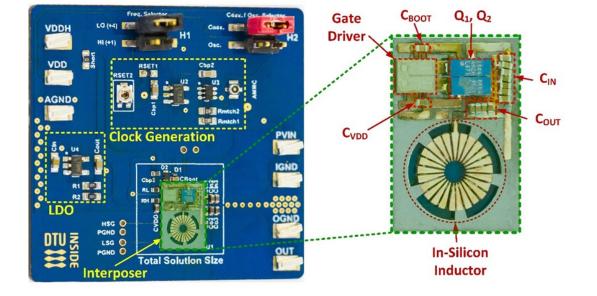
Bottom

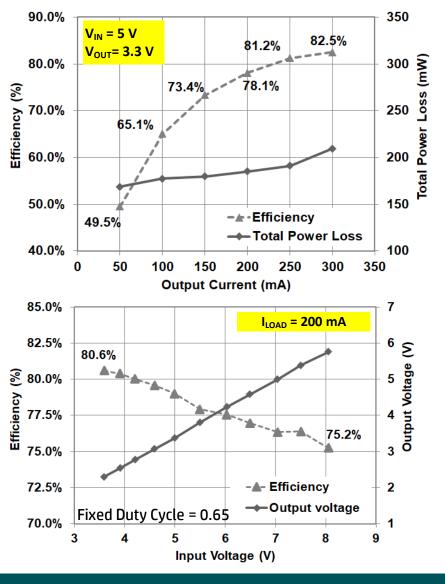
KHI DOOK

with - At Lame

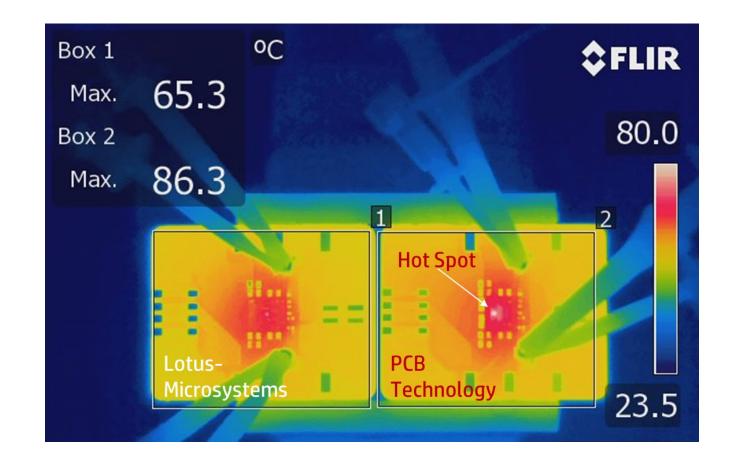
1st Power Interposer – Technical Univ. of Denmark 2018 Unicrosystems

Prototype Functional Testing Results







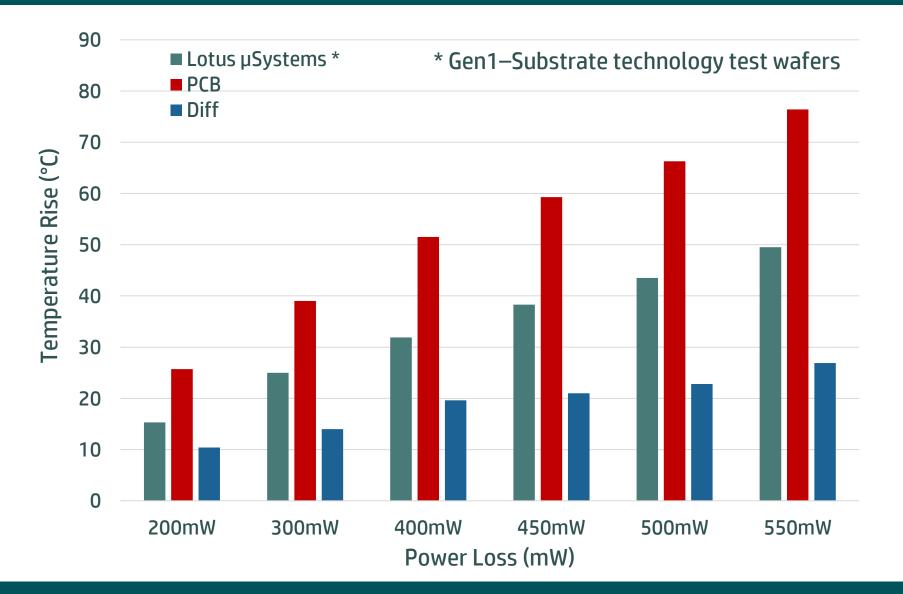


Notes

 Plots are extracted from Measured Data of Gen1– Substrate technology test chip.

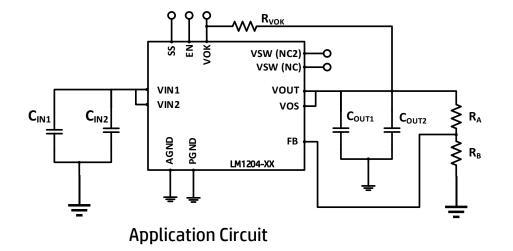
Lotus Microsystems' Substrate Thermal Performance





The LM1204X family is a range of miniaturized 16V step-down converters, offering very compact size and high efficiency.

The module includes control, power switches, and magnetics in one compact package.



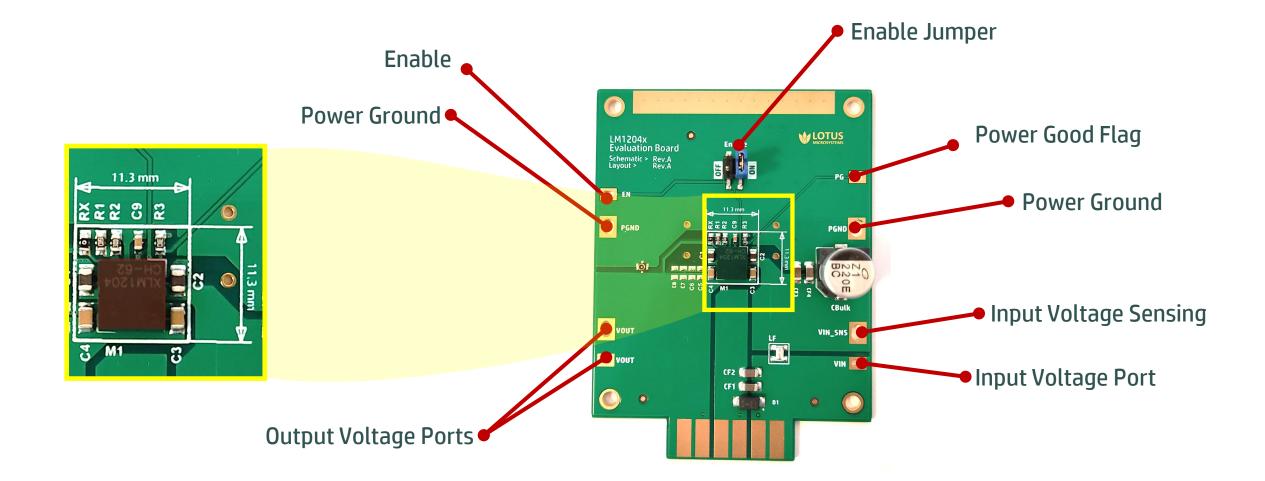
Features

- 4.2V to 16.8V input voltage range
- > 4 A continuous operation
- > 1V to 3.3V output voltage range
- Integrated magnetics
- Low output ripple.
- Internal loop compensation
- > OTP, SCP, OCP and UVLO protection



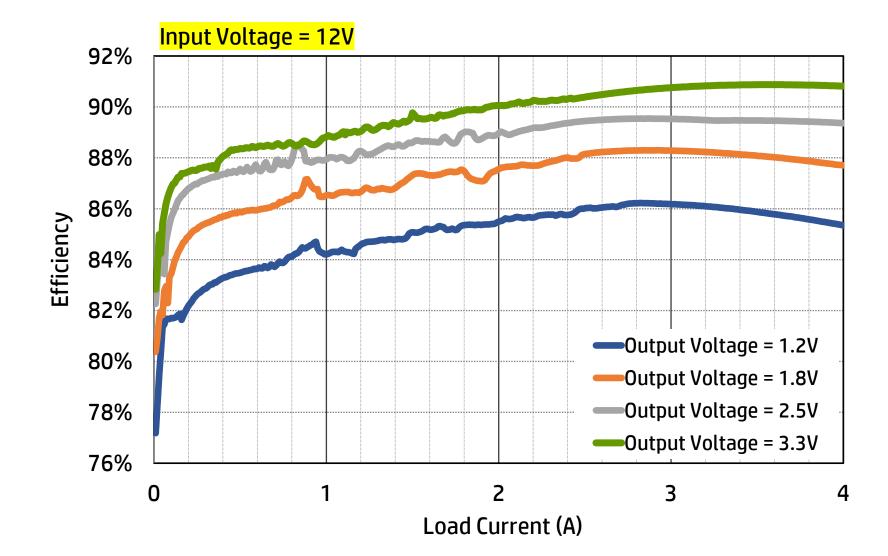
Lotus Microsystems LM1204X Converters





Lotus Microsystems LM1204X Converters





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